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NUP8011MU

ESD Protection Diode Array Low Clamping Voltage

This integrated surge protection device is designed for applications requiring transient overvoltage protection. It is intended for use in sensitive equipment such as computers, printers, business machines, communication systems, and other applications. Its integrated design provides very effective and reliable protection for eight separate lines using only one package. These devices are ideal for situations where board space is at a premium.

Features

- Low Clamping Voltage
- UDFN Package, 1.2 x 1.8 mm
- Standoff Voltage: 4.3 V
- Low Leakage Current
- IEC61000-4-2, Level 4 ESD Protection
- Moisture Sensitivity Level 1
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Benefits

- Provides Protection for ESD Industry Standards: IEC 61000, HBM
- Protects the Line Against Transient Voltage Conditions
- Minimize Power Consumption of the System
- Minimize PCB Board Space

Applications

- ESD Protection for Data Lines
- Wireless Phones
- Handheld Products
- Notebook Computers
- LCD Displays

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Value	Unit
Steady State Power – 1 Diode (Note 1)	PD	380	mW
Thermal Resistance, Junction-to-Ambient Above 25°C, Derate	R _{θJA}	327 3.05	°C/W mW/°C
Maximum Junction Temperature	T _{Jmax}	150	°C
Operating Temperature Range	T _{OP}	-40 to +85	°C
Storage Temperature Range	T _{stg}	–55 to +150	°C
Lead Solder Temperature (10 seconds duration)	ΤL	260	°C
IEC 61000-4-2 (ESD)Contact		±8.0	kV
Machine Model - Class C	MM	400	V
Human Body Model – Class 3B	HBM	8.0	kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

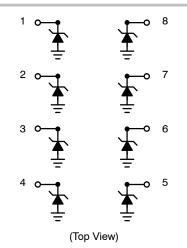
1. Only 1 diode under power. For all 4 diodes under power, P_D will be 25%. Mounted on FR-4 board with min pad.

See Application Note AND8308/D for further description of survivability specs.



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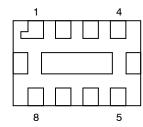


MARKING DIAGRAM P3 M UDFN8 CASE 517AD

P3 = Specific Device Code Μ

- = Month Code
- = Pb-Free Package

PIN CONNECTIONS



ORDERING INFORMATION

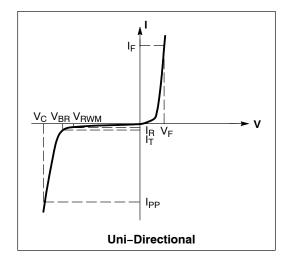
Device	Package	Shipping
NUP8011MUTAG	UDFN8 (Pb–Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

Symbol	Parameter					
I _{PP}	Maximum Reverse Peak Pulse Current					
V _C	Clamping Voltage @ I _{PP}					
V _{RWM}	Working Peak Reverse Voltage					
I _R	Maximum Reverse Leakage Current @ V _{RWM}					
V _{BR}	Breakdown Voltage @ I _T					
Ι _Τ	Test Current					
١ _F	Forward Current					
V _F	Forward Voltage @ I _F					
P _{pk}	Peak Power Dissipation					
С	Capacitance @ $V_R = 0$ and f = 1.0 MHz					



*See Application Note AND8308/D for detailed explanations of datasheet parameters.

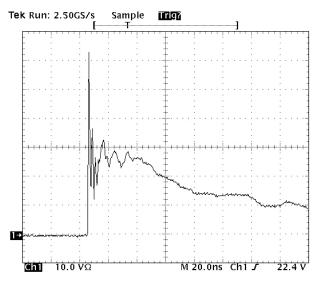
ELECTRICAL CHARACTERISTICS (T_A = 25°C)

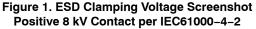
			Breakdown Voltage V _{BR} @ 1 mA (V)		Leakage Current I _{RM} @ V _{RM}		Typ Cap @ 0 V B (Not	ias (pF)	Typ Capa @ 3 V B (Not	ias (pF)	v _c
Device	Device Marking	Min	Nom	Max	V _{RWM}	I _{RWM} (μΑ)	Тур	Max	Тур	Max	Per IEC61000-4-2 (Note 3)
NUP8011MUTAG	P3	6.47	6.8	7.14	4.3	1.0	12	14	6.7	9.5	Figures 1 and 2 (See Below)

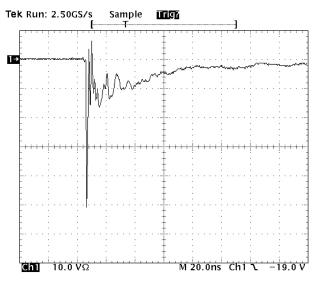
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Capacitance of one diode at f = 1 MHz, $V_R = 0$ V, $T_A = 25^{\circ}C$

3. For test procedure see Figures 3 and 4 and Application Note AND8307/D.









NUP8011MU

IEC 61000-4-2 Spec.

Level	Test Volt- age (kV)			Current at 60 ns (A)	
1	2	7.5	4	2	
2	4	15	8	4	
3	6	22.5	12	6	
4	8	30	16	8	

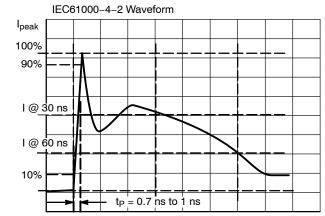


Figure 3. IEC61000-4-2 Spec

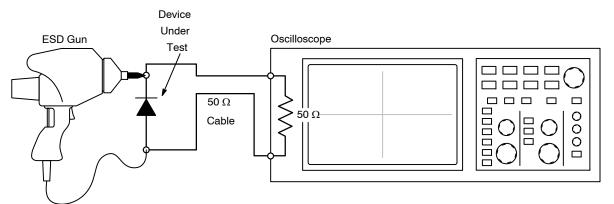


Figure 4. Diagram of ESD Test Setup

The following is taken from Application Note AND8308/D – Interpretation of Datasheet Parameters for ESD Devices.

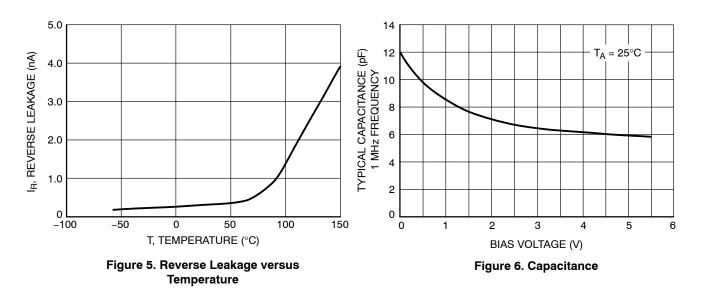
ESD Voltage Clamping

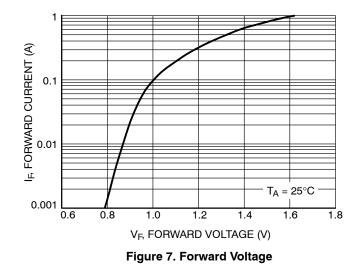
For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000–4–2 waveform. Since the IEC61000–4–2 was written as a pass/fail spec for larger

systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.

NUP8011MU

TYPICAL ELECTRICAL CHARACTERISTICS

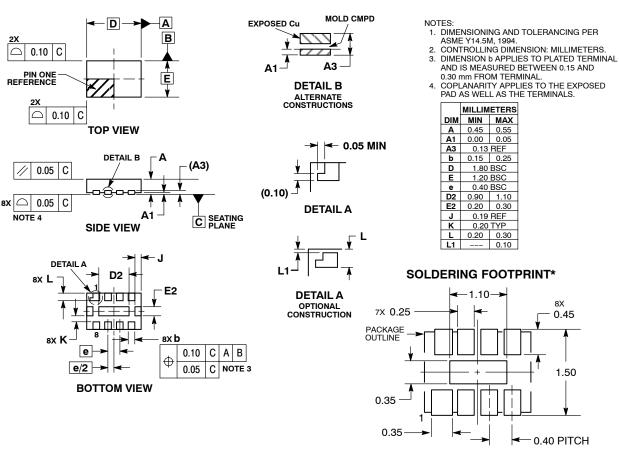




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PACKAGE DIMENSIONS

UDFN8, 1.8 x 1.2, 0.4P CASE 517AD ISSUE D



DIMENSIONS: MILLIMETERS

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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